### Status of Radioactive Ion Beams at the HRIBF



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OAK RIDGE NATIONAL LABORATORY U.S. Department of Energy



# **The HRIBF: an ISOL RIB facility**







## **Ion Sources used for RIB Production**

- Electron Beam Plasma Ion Source
  - High positive ionization efficiency for many elements
  - >1000 hrs (5000  $\mu$ Ah) mean lifetime in beam
- Kinetic Ejection Negative Ion Source
  - Used for production of <sup>17,18</sup>F beams
  - >1200 hrs (3000  $\mu$ Ah) mean lifetime in beam
- **Negative Surface Ionization (LaB<sub>6</sub> surface)** 
  - Specific for Group VIIA elements
  - High efficiency and good emittance
- Batch-mode Cs-sputter Negative Ion Source
  - On-line production of long-lived nuclei (e.g. <sup>56</sup>Ni)



# **RIB Production Targets**

- HfO<sub>2</sub> fibers (production of <sup>17</sup>F and <sup>18</sup>F)
- **Uranium Carbide** (production of n-rich beams)
- Molten metals
  - Germanium for production of As and Ga isotopes
  - Nickel for production of Cu isotopes
- Ni pellets (production of <sup>56</sup>Ni via (p,p2n) reaction)
- Silicon Carbide (production of <sup>25</sup>Al and <sup>26</sup>Al)
  - Fibers (15  $\mu$ m) and powder (1  $\mu$ m)
- **Cerium Sulfide** (production of <sup>33</sup>Cl and <sup>34</sup>Cl)
  - Thin layers deposited on W-coated carbon matrix
- Pd powders (production of p-rich Ag isotopes)



### HfO<sub>2</sub> Fiber Target for Production of <sup>17,18</sup>F Beams

HfO<sub>2</sub>

- Thin Fibers (5 μm) fast diffusion
- High porosity (density is 1.15 g/cm<sup>3</sup>)
- Refractory (m.p. is 2770 C)
- Free of volatile impurities
- 4 rolls of HfO<sub>2</sub> cloth used for target
  - 1.5 cm diameter x 1 cm thick each
  - Range of 42 MeV deuterons is 1.6 cm
- Al<sub>2</sub>O<sub>3</sub> felt sheath
  - Provides aluminum vapor
  - Transported as AIF molecule



JT-BATTELLE

Al2O3

Beam

#### Uncoated RVCF

UC<sub>2</sub> Coated RVCF Thickness: ~10 µm





- RVC fiber diameter: 60 μm
- Matrix density: 0.06 g/cm<sup>3</sup>
- UC coating thickness: 8 10 mm
- Target density: 1.17 g/cm<sup>3</sup>
- Uranium target thickness: 2.1 g/cm<sup>2</sup>

110

- Mass ratio is U:C::6.6:1
- Atomic ratio is UC<sub>3</sub>

80

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**UC Targets for** 

**Production of** 

**Neutron-rich Beams** 

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#### **On-Line Target and Ion Source Testing Facility**



# **On-line Target and Ion Source Testing**

- An independent, low intensity test facility is an important and unique capability
- Makes use of a pre-existing separator
- Measure characteristics of the targets and ion sources
  - release from the target
  - transport from target to ion source
  - ion source efficiency (especially at high target temperatures)
- Compatible with the RIB Injector Platform
  - mechanically identical
  - operational experience is transportable
  - results are scaleable (10 nA to 10  $\mu\text{A}\text{)}$
- Dual function as test facility and TIS quality assurance



### **Proton-rich Radioactive Ion Beams**



OAK RIDGE NATIONAL LABORATORY U.S. DEPARTMENT OF ENERGY List of available beams on HRIBF website at <u>www.phy.ornl.gov/hribf/users/beams/</u>

#### Available Neutron-rich Radioactive Ion Beams (over 100 beams with intensities $\geq 10^3$ ions/sec)



OAK RIDGE NATIONAL LABORATORY U.S. Department of Energy List of available beams on HRIBF website at www.phy.ornl.gov/hribf/users/beams/

# Accelerated proton-rich Radioactive Ion Beams

RIB	Energy Range	Highest Intensity	<b>ORIC</b> Current	Purity
	(MeV)	(pps on target)	(µA on target)	(%)
<sup>17</sup> F	10-170	<b>1.0 x 10<sup>7</sup></b>	3	100
<sup>18</sup> F	10-25	3.0 x 10 <sup>5</sup>	1	10
<sup>67</sup> Ga*	160	2.5 x 10 <sup>5</sup>	5	> 90
<sup>69</sup> As	160	2.0 x 10 <sup>6</sup>	5	~ 10
<sup>70</sup> As*	140	$2.0 \times 10^3$	0.01	< 10 <sup>-6</sup>

\* These beams were used for commissioning runs



#### **Accelerated n-rich Radioactive Ion Beams**

RIB	<b>Energy Range</b>	<b>Highest Intensity</b>	ORIC Current	Purity
	(MeV)	(pps on target)	(µA on target)	(%)
<sup>78</sup> Ge	175	1.5 x 10 <sup>6</sup>	7	38
<sup>80</sup> Ge	179	<b>1.8 x 10<sup>6</sup></b>	7	10
<sup>117</sup> Ag*	460	<b>1.2 x 10</b> <sup>6</sup>	9	95
<sup>118</sup> Ag	455	1.5 x 10 <sup>6</sup>	11	90
<sup>126</sup> Sn	378	<b>1.0 x 10<sup>7</sup></b>	5	50
<sup>128</sup> Sn	384	2.5 x 10 <sup>6</sup>	5	20
<sup>132</sup> Te	350-396	5.0 x 10 <sup>6</sup>	5	87
<sup>134</sup> Te	396-560	2.4 x 10 <sup>6</sup>	7	70
<sup>136</sup> Te	396	<b>5.0</b> x 10 <sup>5</sup>	7	50

\* Used for commissioning OAK RIDGE NATIONAL LABORATORY U.S. DEPARTMENT OF ENERGY



#### Accelerated Ion Beams <u>Now Available</u> at the HRIBF



# **Improving the n-rich RIB Yields**

- Beam purity
  - ionization selectivity
  - chemistry in the target and ion source
  - lower emittance to improve isobar separation
  - selective charge exchange schemes
- Beam intensity
  - higher production rates
    - raster the beam across the target
    - more refractory targets
    - faster dissipation of heat from the target
  - more efficient transport of short-lived nuclei
  - ion sources with higher ionization efficiencies



# **Pure Sn Beams**

- Most of the neutron-rich Sn beams are contaminated
  - A=132 beam consists of 87% Te, 12% Sb, and 1% Sn
- Solution: extract from EBP ion source as SnS<sup>+</sup>
- Sulfur is added to the UC target via H<sub>2</sub>S gas
- No detectable TeS<sup>+</sup> or SbS<sup>+</sup> ions
- Convert SnS<sup>+</sup> to Sn<sup>-</sup> in a Cs-vapor cell
- Energy spread is ~400 eV (molecular breakup)
- Selection process is unknown
  - do TeS and SbS dissociate due to high target temperature
  - do these molecules breakup during the ionization process
  - why don't the oxides behave in a similar manner
- Pure Ge beams are also available using this technique



**Intensity of Sn<sup>-</sup> beams injected into the Tandem (from SnS<sup>+</sup>)** (the solid line is the production rate in the target, normalized to <sup>127</sup>Sn)





#### **Ratios of positive ion yields for Sn isotopes** (SnS<sup>+</sup> and Sn<sup>+</sup> from a UC target)





# Pure Br and I Beams

- Release efficiency of Br and I from UC target is high
- Charge exchange efficiency in Cs-cell is low (0.8%)
- Solution: make negative ions directly using negative surface ionization from a hot LaB<sub>6</sub> surface
  - 15% efficiency for stable Br<sup>-</sup> beams
- Br negative ion yields are 25 times greater than with EBPIS followed by charge exchange
- Yields are 10 times greater for iodine
- Expect at least 10<sup>5</sup> pps on target for <sup>89</sup>Br and <sup>137</sup>I (8 neutrons beyond last stable isotope)
- Br beams are pure (no Se or Rb observed)
- I beams are pure (no Sn, Sb, Te, or Cs)



## **Pure Rb Beams**

- Rb release from target is quite fast
- Positive ion sources using surface ionization have high efficiencies for Rb (>90% ISOLDE)
- Ionizer is a hot Ta or W tubular surface
- Charge exchange efficiency in Cs-cell is 0.3%
- Sr is also ionized efficiently but at higher operating temperatures
- Should result in at least a factor of 10 increase over present yields with higher beam purity
- Expect to deliver to experiments at least 10<sup>5</sup> pps for Rb isotopes out to <sup>94</sup>Rb (7 neutrons beyond stability)



# **Other Targets and Beams in Development**

- <sup>25</sup>Al from SiC
  - already tested fibers (15  $\mu\text{m}$  dia.) and powder (1  $\mu\text{m}\,$  dia.)
  - $^{25}\text{AI}$  yield in both cases was low (10<sup>4</sup> pps/µA from EBPIS)
  - thin layer of SiC deposited on low-density RVC matrix
- Optimize UC targets
  - vary the uranium density and matrix porosity
- <sup>33</sup>Cl from CeS
  - 1  $\mu$ m dia. powder suspended in low-density matrix
  - LaB<sub>6</sub> surface ion source (negative)
- <sup>26</sup>Si and <sup>27</sup>Si from Al<sub>2</sub>O<sub>3</sub> target
  - use technique developed for Sn and Ge (extract as SiS<sup>+</sup>)
- Pd target for proton-rich Ag beams
  - complements the n-rich Ag beams from UC target
- <sup>7</sup>Be beams from a multi-sample Cs-sputter ion source



#### **RIB Development Personnel**

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